

mole fraction of DCS

$$y_{DCS} = \frac{Q_{DCS}}{Q_{NH_3} + Q_{DCS}} = \frac{70 \text{ sccm}}{100 \text{ sccm} + 70 \text{ sccm}}$$
$$y_{DCS} = 0.2593$$

Concentration of DCS

$$780 \times 10^{-3} \text{ Torr} \times \frac{133.322 \text{ Pa}}{1 \text{ Torr}} = 33.33 \text{ Pa}$$

$$\frac{n}{V} = \frac{P_g}{RT} = \frac{(0.2593)(33.33 \text{ Pa})}{(8.314 \text{ J/(K}\cdot\text{mol)})(770 + 273) \text{ K}}$$

$$C_{DCS} = 9.97 \times 10^{-4} \text{ mol/m}^3$$

kinetic Eq'n

$$J = k_0 \exp \left[\frac{-E_a}{RT} \right] C_{DCS}^{0.49}$$
$$= 82300 \text{ s}^{-1} \exp \left[\frac{-(169.4 \times 10^3 \text{ J/mol})}{(8.314 \text{ J/(K}\cdot\text{mol)})(770 + 273) \text{ K}} \right] (9.97 \times 10^{-4} \text{ mol/m}^3)^{0.49}$$
$$= 9.14 \times 10^{-6} \text{ mol/(cm}^2\cdot\text{s)} \quad \text{rate of change of } C_{DCS}$$

Deposition rate

Stoichiometric coefficient $\text{SiCl}_2\text{H}_2 : \text{Si}_3\text{N}_4 = 3 : 1$

approximate deposition rate $\approx \frac{1}{3} (9.14 \times 10^{-6} \text{ mol/(cm}^2\cdot\text{s)}) \approx 3.05 \times 10^{-6} \text{ mol/(cm}^2\cdot\text{s)}$
by neglecting surface kinetics.

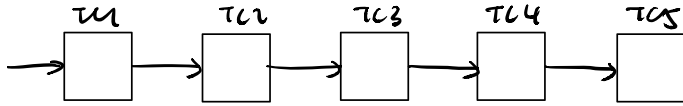
$$\text{MW}_{\text{Si}_3\text{N}_4} = 140.28 \text{ g/mol}$$

$$\rho_{\text{Si}_3\text{N}_4} = 3000 \text{ kg/m}^3$$

$$\frac{3.05 \times 10^{-6} \text{ mol}}{\text{m}^2\cdot\text{s}} \times \frac{140.28 \text{ g}}{\text{mol}} \times \frac{\text{m}^3}{3000 \times 10^3 \text{ g}} = 1.43 \times 10^{-10} \text{ m/s}$$

$$\boxed{\text{deposition rate} = 1.43 \text{ \AA/s} = 85.8 \text{ \AA/min}}$$

$$\frac{1000 \text{ \AA}}{85.8 \text{ \AA/min}} = 23.31 \text{ mm} \approx 25 \text{ mm}.$$



40 wafers each

$$\text{Volume of Si}_3\text{N}_4 = (\pi)(100)(\pi)(0.15\text{m})^2(1000 \times 10^{-10}\text{m})$$

$$= 2.83 \times 10^{-6} \text{ m}^3$$

$$\eta_{\text{Si}_3\text{N}_4} = (2.83 \times 10^{-6} \text{ m}^3) \left(\frac{3000 \text{ kg}}{\text{m}^3} \right) \left(\frac{1 \text{ mol}}{0.14 \text{ kg}} \right)$$

$$\eta_{\text{Si}_3\text{N}_4} = 0.061 \text{ mol} \quad \text{which is} \quad \eta_{\text{DCS}} = 0.183 \text{ mol}$$

0.0813 mol Si_3N_4 for 20 sccm DCS flow
 100 sccm Si_3N_4 flow
 which is 0.144 mol of DCS

material balance on DCS

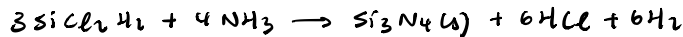
$$\dot{n}_{\text{in}} - \text{out} + \text{gen} - \text{cons} = \text{acc}$$

$$\dot{n}_{\text{in}} - \text{out} - \text{cons} = 0$$

$$0.144 \text{ mol} - \text{out} - \left(\frac{0.183 \text{ mol}}{100} \right) (40) = 0$$

$$\boxed{\text{out} = 0.1074 \text{ mol}} \quad \text{TC1}$$

overall chem eq'n



At the end of TC1

	Z	C	P
SiCl_2H_2	0.144	-0.0366	0.1074
NH_3	0.813	-0.0488	0.7642
HCl	0	+0.0732	0.0732
H_2	0	+0.0732	0.0732

$$\eta_{\text{DCS, TC1}} = \frac{0.1074}{0.1074 + 0.7642 + 0.0732 + 0.0732}$$

$$\eta_{\text{DCS, TC1}} = 0.1855$$

concentration of DCS exiting TC1 / entering TC2

$$\frac{n}{V} = \frac{P_A}{RT}$$

	η (mol)
Si_3N_4	0.0813
SiCl_2H_2	0.1439
NH_3	0.813